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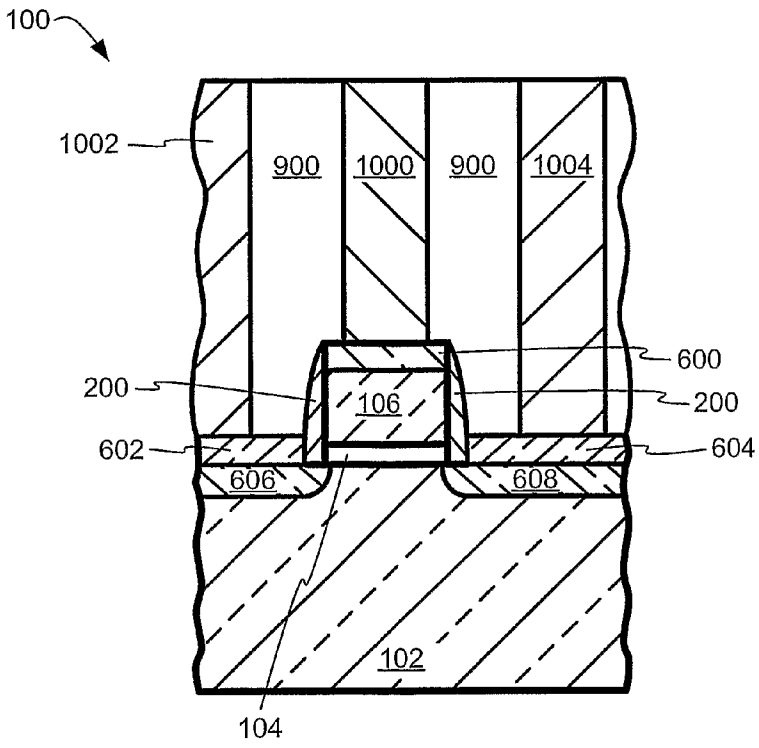
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(54) Title: FORMATION OF ABRUPT JUNCTIONS IN DEVICES BY USING SILICIDE GROWTH DOPANT SNOWPLOW EFFECT



(57) Abstract: A method (1100) of forming an abrupt junction device (100) with a semiconductor substrate (102) is provided. A gate dielectric (104) is formed (1104) on a semiconductor substrate (102), and a gate (106) is formed (1106) on the gate dielectric (104). A sidewall spacer (200) is formed (1108) on the semiconductor substrate (102) adjacent the gate (106) and the gate dielectric (104). A thickening layer (300) is formed (1110) by selective epitaxial growth on the semiconductor substrate (102) adjacent the sidewall spacer (200). Raised source/drain dopant implanted regions (402, 404) are formed (1112) in at least a portion of the thickening layer (300). Silicide layers (602, 604) are formed (1114) in at least a portion of the raised source/drain dopant implanted regions (402, 404) to form source/drain regions (606, 608), beneath the silicide layers (602, 604), that are enriched with dopant from the silicide layers (602, 604). A dielectric layer (900) is deposited over the silicide layers (602, 604), and contacts (1002, 1004) are then formed in the dielectric layer (900) to the silicide layers (602, 604).

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